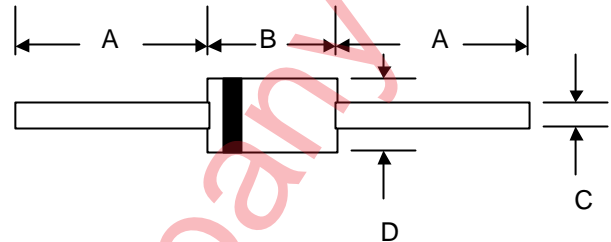


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Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop, High Efficiency
- Low Power Loss
- Fast Recovery Time
- High Surge Current Capability



Mechanical Data

- Case: Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Mounting Position: Any
- Weight: 0.21 grams (approx.)

DO-201AD				
Dim	Min	Max	Min	Max
A	25.4	—	1.000	—
B	8.50	9.50	0.335	0.374
C	1.20	1.30	0.047	0.051
D	5.0	5.60	0.197	0.220
All	In mm		In inch	

Maximum Ratings and Electrical Characteristics @ $T_A=25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	MR850	MR851	MR852	MR854	MR856	MR858	Unit
Peak Repetitive Reverse Voltage	V_{RRM}							V
Working Peak Reverse Voltage	V_{RWM}	50	100	200	400	600	800	
DC Blocking Voltage	V_R							
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	V
Average Rectified Output Current @ $T_L = 75^\circ\text{C}$	I_o	3.0						A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	150						A
Forward Voltage @ $I_F = 3.0\text{A}$	V_{FM}	1.25				1.30		V
Peak Reverse Current @ $T_A = 25^\circ\text{C}$ At Rated DC Blocking Voltage @ $T_A = 100^\circ\text{C}$	I_{RM}	10 200						μA
Reverse Recovery Time (Note 1)	t_{rr}	100				150		nS
Typical Junction Capacitance (Note 2)	C_j	80						pF
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150						$^\circ\text{C}$

Note: 1. Measured with $I_F = 0.5\text{A}$, $I_R = 1.0\text{A}$, $I_T = 0.25\text{A}$,
2. Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.

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RATINGS AND CHARACTERISTIC CURVES (MR850-MR858)

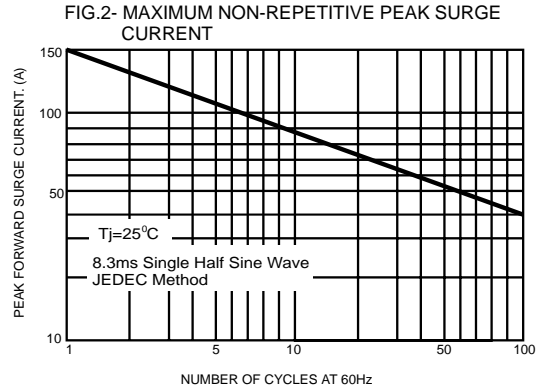
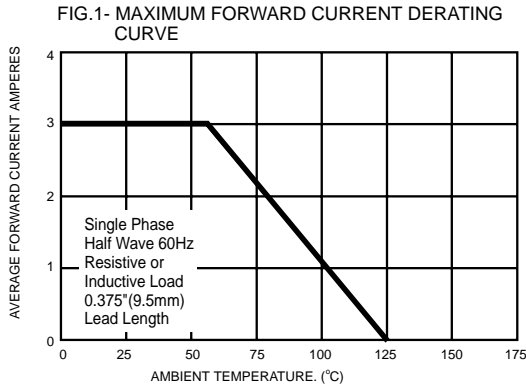


FIG.3- TYPICAL FORWARD CHARACTERISTICS

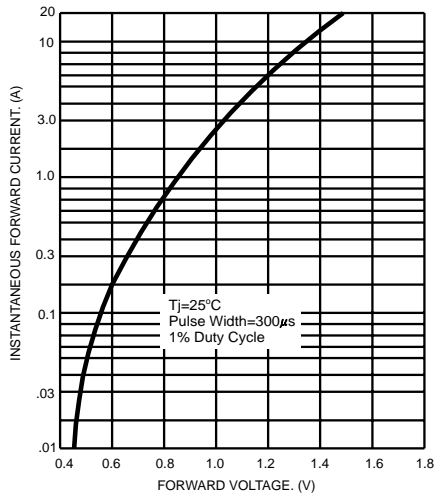


FIG.4- TYPICAL JUNCTION CAPACITANCE

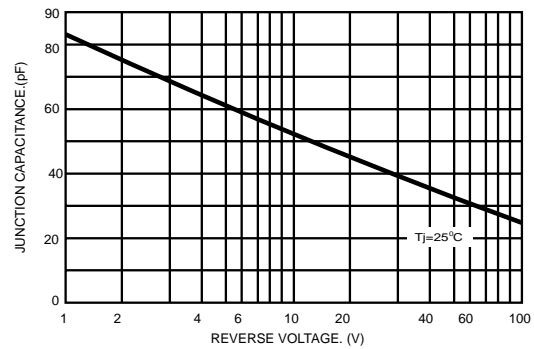
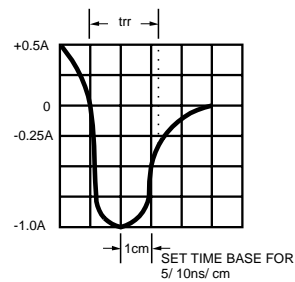
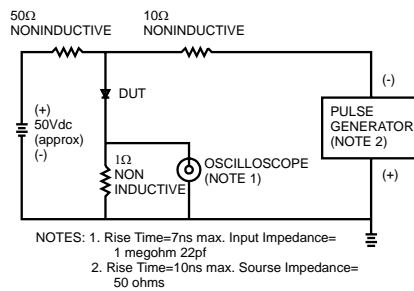


FIG.5- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



TECHNICAL DATA

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